

## High Speed CMOS Logic Octal Three-State Bus Transceiver, Inverting

January 1998

### Features

- Buffered Inputs
- Three-State Outputs
- Applications in Multiple-Data-Bus Architecture
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}$ ,  $V_{OH}$

### Description

The Harris CD74HC640 and CD74HCT640 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads. The CD74HC640 and CD74HCT640 are inverting buffers.

The direction of data flow (A to B, B to A) is controlled by the DIR input.

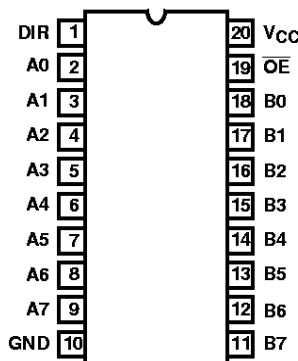
Outputs are enabled by a low on the Output Enable input ( $\overline{OE}$ ); a high  $\overline{OE}$  puts these devices in the high impedance mode.

### Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC640E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT640E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT640M	-55 to 125	20 Ld SOIC	M20.3

### Pinout

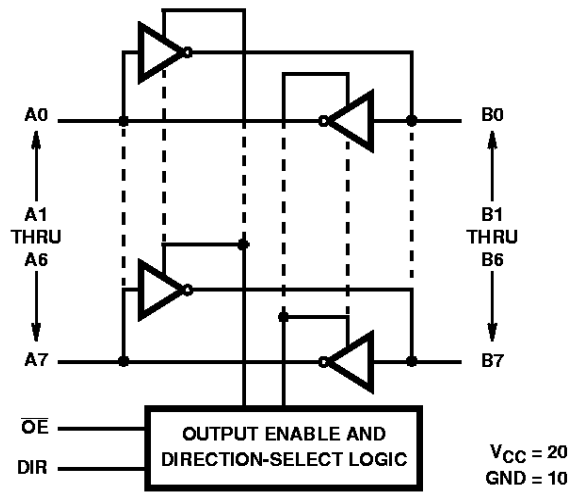
CD74HC640, CD74HCT640  
(PDIP, SOIC)  
TOP VIEW



### NOTE:

1. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

**Functional Diagram**



**TRUTH TABLE**

CONTROL INPUTS		DATA PORT STATUS	
$\overline{OE}$	DIR	$A_n$	$B_n$
L	L	$\overline{O}$	I
H	H	Z	Z
H	L	Z	Z
L	H	I	$\overline{O}$

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with 1k $\Omega$  to 1M $\Omega$  resistors.

- H = High Level
- L = Low Level
- I = Input
- $\overline{O}$  = Output (Inversion of Input Level)
- Z = High Impedance

# CD74HC640, CD74HCT640

## Absolute Maximum Ratings

DC Supply Voltage, $V_{CC}$ .....	-0.5V to 7V
DC Input Diode Current, $I_{IK}$	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Output Diode Current, $I_{OK}$	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Drain Current, per Output, $I_O$	
For $-0.5V < V_O < V_{CC} + 0.5V$ .....	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, $I_O$	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ .....	$\pm 25mA$
DC $V_{CC}$ or Ground Current, $I_{CC}$ .....	$\pm 50mA$

## Thermal Information

Thermal Resistance (Typical, Note 2)	$\theta_{JA}$ ( $^{\circ}C/W$ )
PDIP Package .....	125
SOIC Package .....	120
Maximum Junction Temperature .....	$150^{\circ}C$
Maximum Storage Temperature Range .....	$-65^{\circ}C$ to $150^{\circ}C$
Maximum Lead Temperature (Soldering 10s) .....	$300^{\circ}C$
(SOIC - Lead Tips Only)	

## Operating Conditions

Temperature Range, $T_A$ .....	$-55^{\circ}C$ to $125^{\circ}C$
Supply Voltage Range, $V_{CC}$	
HC Types .....	2V to 6V
HCT Types .....	4.5V to 5.5V
DC Input or Output Voltage, $V_I, V_O$ .....	0V to $V_{CC}$
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

### NOTE:

- $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		$V_{CC}$ (V)	25 $^{\circ}C$			-40 $^{\circ}C$ TO 85 $^{\circ}C$		-55 $^{\circ}C$ TO 125 $^{\circ}C$		UNITS	
		$V_I$ (V)	$I_O$ (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX		
<b>HC TYPES</b>													
High Level Input Voltage	$V_{IH}$	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	$V_{IL}$	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
High Level Output Voltage CMOS Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-0.02	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-	-	-	-	-	-	-	-	-	V	
			-6	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	0.02	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	-	-	-	-	-	-	-	-	-	V	
			6	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	$I_I$	$V_{CC}$ or GND	-	-	6	-	-	$\pm 0.1$	-	$\pm 1$	-	$\pm 1$	$\mu A$

## CD74HC640, CD74HCT640

### DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5	-	±10	μA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> and GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5	-	-	±0.5	-	±5	-	±10	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE: For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

### HCT Input Loading Table

INPUT	UNIT LOADS
DIR	0.9
OE, A	1.5
B	1.5

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Table, e.g., 360μA max at 25°C.

## CD74HC640, CD74HCT640

### Switching Specifications $C_L = 50\text{pF}$ , Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC}$ (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNIT S
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
Propagation Delay A to $\bar{B}$ B to $\bar{A}$	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	90	-	115	-	135	ns
			4.5	-	-	18	-	23	-	27	ns
		$C_L = 15\text{pF}$	5	-	7	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	15	-	20	-	23	ns
Output High-Z To High Level, To Low Level	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output High Level Output Low Level to High Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	$C_{PD}$	-	5	-	38	-	-	-	-	-	pF
<b>HCT TYPES</b>											
Propagation Delay A to $\bar{B}$ B to $\bar{A}$	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	22	-	28	-	33	ns
		$C_L = 15\text{pF}$	5	-	9	-	-	-	-	-	ns
Output High-Z To High Level, To Low Level	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
Output High Level Output Low Level to High Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	$C_{PD}$	-	5	-	41	-	-	-	-	-	pF

**NOTES:**

3.  $C_{PD}$  is used to determine the dynamic power consumption, per channel.
4.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

Test Circuits and Waveforms

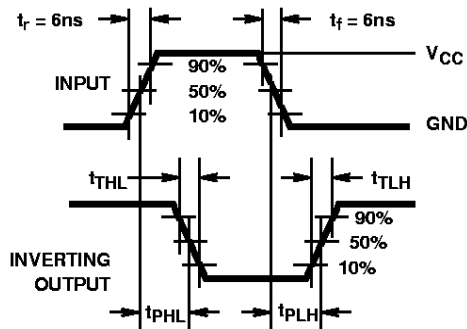


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

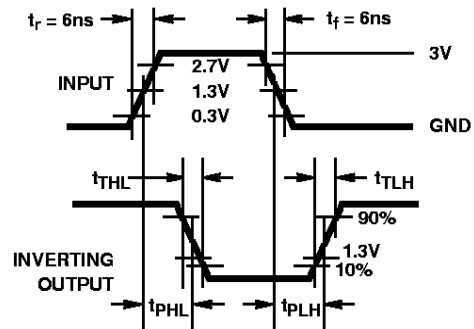


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

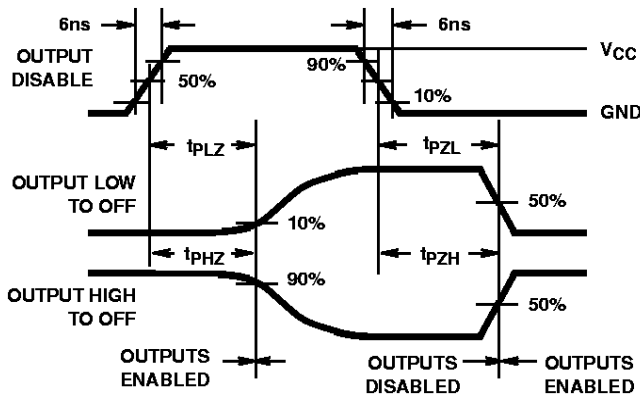


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

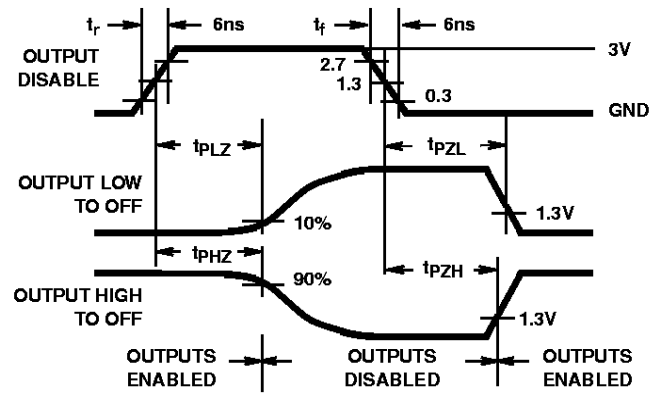
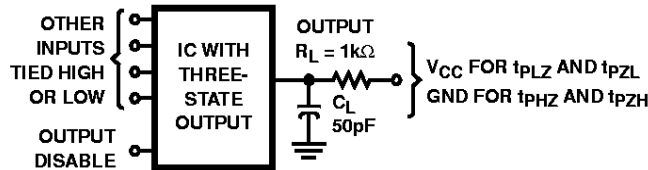


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$  to  $V_{CC}$ ,  $C_L = 50pF$ .

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT